# BD436G, BD438G, BD440G, BD442G

## **Plastic Medium Power** Silicon PNP Transistor

This series of plastic, medium–power silicon PNP transistors can be used for for amplifier and switching applications. Complementary types are BD437 and BD441.

#### Features

• These Devices are Pb-Free and are RoHS Compliant\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage BD436G BD438G BD440G BD442G	V <sub>CEO</sub>	32 45 60 80	Vdc
Collector–Base Voltage BD436G BD438G BD440G BD442G	V <sub>CBO</sub>	32 45 60 80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current	۱ <sub>C</sub>	4.0	Adc
Base Current	Ι <sub>Β</sub>	1.0	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	36 288	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

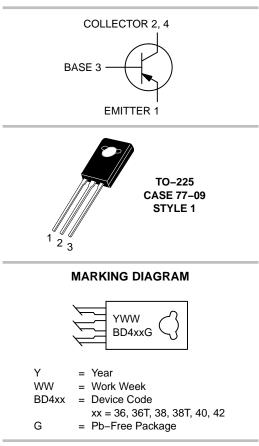
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.5	°C/W



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## 4.0 AMP POWER TRANSISTORS PNP SILICON



### **ORDERING INFORMATION**

Device	Package	Shipping
BD436G	TO–225 (Pb–Free)	500 Units/Box
BD436TG	TO–225 (Pb–Free)	50 Units/Rail
BD438G	TO–225 (Pb–Free)	500 Units/Box
BD438TG	TO–225 (Pb–Free)	50 Units/Rail
BD440G	TO-225 (Pb-Free)	500 Units/Box
BD442G	TO–225 (Pb–Free)	500 Units/Box

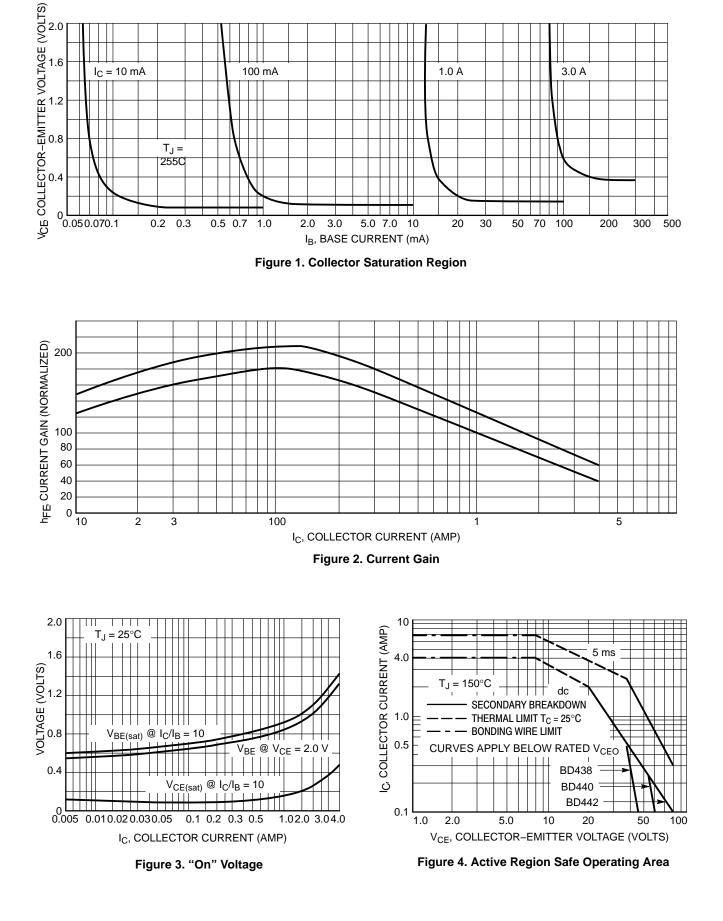
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## BD436G, BD438G, BD440G, BD442G

Characteristic	Symbol	Min	Тур	Max	Unit
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 0) BD436G BD438G BD440G	V <sub>(BR)CEO</sub>	32 45 60			Vdc
BD442G		80	-	-	
Collector–Base Breakdown Voltage ( $I_C = 100 \mu A, I_B = 0$ ) BD436G BD438G BD440G BD442G	V <sub>(BR)CBO</sub>	32 45 60 80	- - - -	- - - -	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 100 \ \mu$ A, $I_C = 0$ )	V <sub>(BR)EBO</sub>	5.0	-	_	Vdc
Collector Cutoff Current $(V_{CB} = 32 V, I_E = 0)$ BD436G	I <sub>CBO</sub>	_	_	0.1	mAdc
$(V_{CB} = 45 \text{ V}, I_E = 0)$ BD438G $(V_{CB} = 60 \text{ V}, I_E = 0)$		-	-	0.1	
BD440G (V <sub>CB</sub> = 80 V, I <sub>E</sub> = 0)		-	-	0.1	
BD442G		-	-	0.1	
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 V)	I <sub>EBO</sub>	-	-	1.0	mAdc
DC Current Gain (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V) BD436G BD438G BD440G BD442G	h <sub>FE</sub>	40 30 20 15	- - - -	- - -	_
DC Current Gain (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 1.0 V) BD436G BD438G BD440G BD442G	h <sub>FE</sub>	85 85 40 40	- - - -	475 475 475 475 475	-
DC Current Gain (I <sub>C</sub> = 2.0 A, V <sub>CE</sub> = 1.0 V) BD436G BD438G BD440G BD442G	h <sub>FE</sub>	50 40 25 15	- - - -	- - - -	-
Collector Saturation Voltage $(I_C = 2.0 \text{ A}, I_B = 0.2 \text{ A})$ BD436G	V <sub>CE(sat)</sub>	_	_	0.5	Vdc
(I <sub>C</sub> = 3.0 A, I <sub>B</sub> = 0.3 A) BD438G BD440G BD442G		- - -	- - -	0.7 0.8 0.8	
Base–Emitter On Voltage (I <sub>C</sub> = 2.0 A, V <sub>CE</sub> = 1.0 V) BD436G/BD438G BD440G/BD442G	V <sub>BE(ON)</sub>	-		1.1 1.5	Vdc
Current–Gain – Bandwidth Product ( $V_{CE} = 1.0 \text{ V}, I_C = 250 \text{ mA}, f = 1.0 \text{ MHz}$ )	fT	3.0	_	-	MHz

### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



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1.0 A

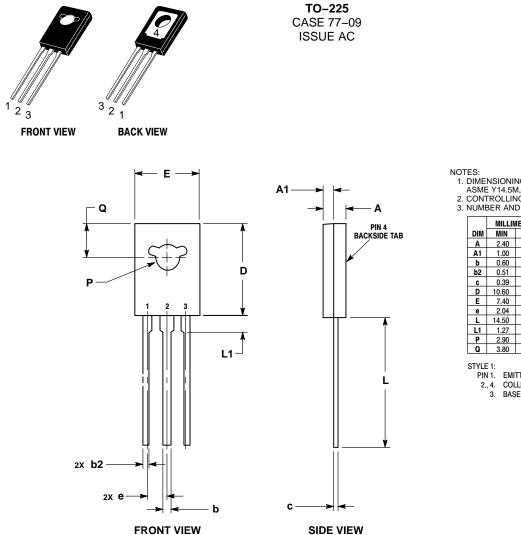
3.0 A

100 mA

 $I_{\rm C} = 10 \text{ mA}$ 

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### PACKAGE DIMENSIONS



NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS.

3. NUMBER AND SHAPE OF LUGS OPTIONAL

MILLIMETERS MIN MAX 3.00 1.50 0.90 0.88 0.63 11.10 7.80 2.54 14.50 16.63 1.27 2.54 2.90 3.30 3.80 4.20 PIN 1 EMITTER COLLECTOR

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